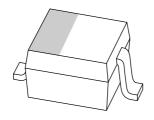
DISCRETE SEMICONDUCTORS

DATA SHEET



1PS76SB10Schottky barrier diode

Product data sheet Supersedes data of 1996 Oct 14 2004 Jan 26



Schottky barrier diode

1PS76SB10

FEATURES

- Low forward voltage
- · Guard ring protected
- Very small plastic SMD package.

APPLICATIONS

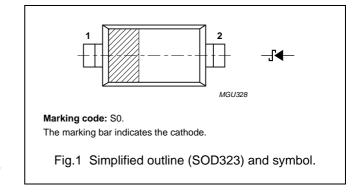
- Ultra high-speed switching
- Voltage clamping
- · Protection circuits
- Blocking diodes.

DESCRIPTION

Planar Schottky barrier diode encapsulated in a SOD323 very small plastic SMD package.

PINNING

PIN	DESCRIPTION
1	cathode
2	anode



ORDERING INFORMATION

TYPE		PACKAGE				
NUMBER	NAME	DESCRIPTION	VERSION			
1PS76SB10	-	plastic surface mounted package; 2 leads	SOD323			

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _R	continuous reverse voltage		_	30	V
I _F	continuous forward current		_	200	mA
I _{FRM}	repetitive peak forward current	$t_p \le 1 \text{ s}; \ \delta \le 0.5$	_	300	mA
I _{FSM}	non-repetitive peak forward current	t _p < 10 ms	_	600	mA
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	125	°C
T _{amb}	operating ambient temperature		-65	+125	°C

Schottky barrier diode

1PS76SB10

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V _F	forward voltage	see Fig.2		
		I _F = 0.1 mA	240	mV
		I _F = 1 mA	320	mV
		I _F = 10 mA	400	mV
		I _F = 30 mA	500	mV
		I _F = 100 mA	800	mV
I _R	reverse current	V _R = 25 V; note 1; see Fig.3	2	μΑ
C _d	diode capacitance	V _R = 1 V; f = 1 MHz; see Fig.4	10	pF

Note

1. Pulsed test: t_p = 300 μ s; δ = 0.02.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	450	K/W

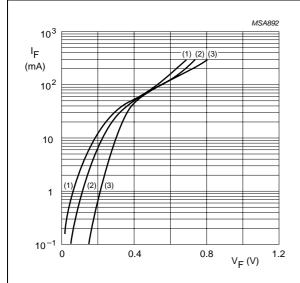
Note

1. Refer to SOD323 standard mounting conditions.

Schottky barrier diode

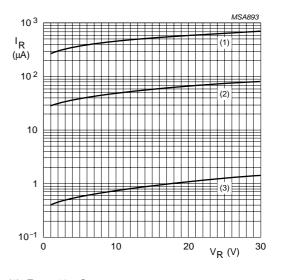
1PS76SB10

GRAPHICAL DATA



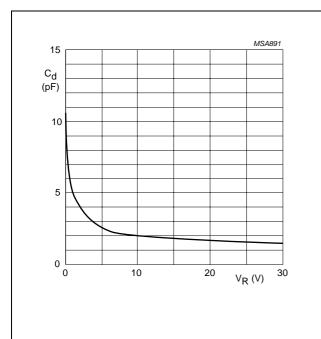
- (1) T_{amb} = 125 °C.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.2 Forward current as a function of forward voltage; typical values.



- (1) $T_{amb} = 125 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.3 Reverse current as a function of reverse voltage; typical values.



 T_{amb} = 25 °C; f = 1 MHz.

Fig.4 Diode capacitance as a function of reverse voltage; typical values.

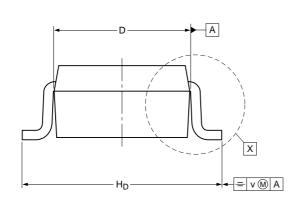
Schottky barrier diode

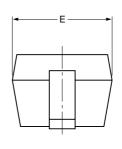
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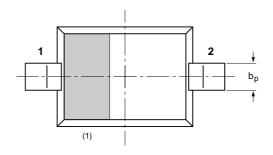
PACKAGE OUTLINE

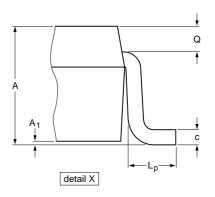
Plastic surface-mounted package; 2 leads

SOD323











DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	bp	С	D	E	H _D	Lp	ø	v
mm	1.1 0.8	0.05	0.40 0.25	0.25 0.10	1.8 1.6	1.35 1.15		0.45 0.15	0.25 0.15	0.2

Note

1. The marking bar indicates the cathode

OUTLINE		REFERENCES				ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOD323			SC-76			03-12-17 06-03-16

Schottky barrier diode

1PS76SB10

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

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